MBC50-x Series

MNOS Series Capacitor Beam Leads

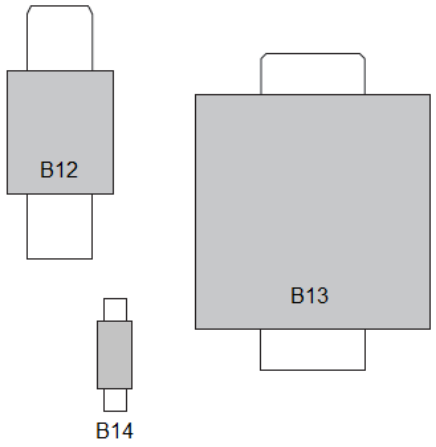
Rev. V1

Features

- Low Leakage Current
- Low Insertion Loss
- Excellent Long Term Stability

Description

The MBC50-x Series capacitors utilize a silicon nitride dielectric over a thermally grown silicon dioxide base. The resultant composite dielectric exhibits low leakage current and insertion loss with excellent long-term stability. The temperature coefficient of capacitance is typically +55 ppm / ºC.

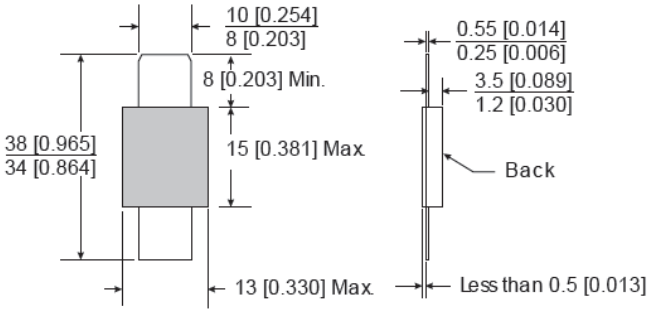


Electrical Specifications: T_A = +25°C

Part #	Total Capacitance (C_T)	Voltage (DWV)	Reverse Current (I_R)	Temperature Coefficient (T_{CC})	Package
	pF	V	mΩ	ppm / °C	
	±20% Typ.	Min.	Min.	Typ.	
MBC50-1B12	1	50	1000	+55	B12
MBC50-2B12	2	50	1000	+55	B12
MBC50-3B12	3	50	1000	+55	B12
MBC50-4B12	4	50	1000	+55	B12
MBC50-6B12	6	50	1000	+55	B12
MBC50-8B12	8	50	1000	+55	B12
MBC50-10B12	10	50	1000	+55	B12
MBC50-15B12	15	50	1000	+55	B12
MBC50-20B12	20	50	1000	+55	B12
MBC50-33B13	33	50	1000	+55	B13
MBC50-47B13	47	50	1000	+55	B13
MBC50-68B13	68	50	1000	+55	B13
MBC50-82B13	82	50	1000	+55	B13
MBC50-100B13	100	50	1000	+55	B13
MBC50-0.2B14	0.2	50	1000	+55	B14
MBC50-1.0B14	1.0	50	1000	+55	B14
MBC50-1.5B14	1.5	50	1000	+55	B14
MBC50-2.0B14	2.0	50	1000	+55	B14
Test Conditions	1 MHz		25 V	-55°C - +200°C	

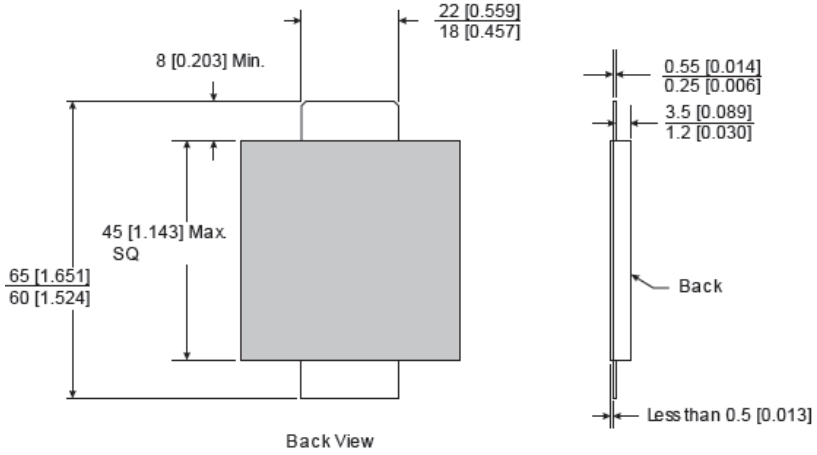
Outline Packages

B12



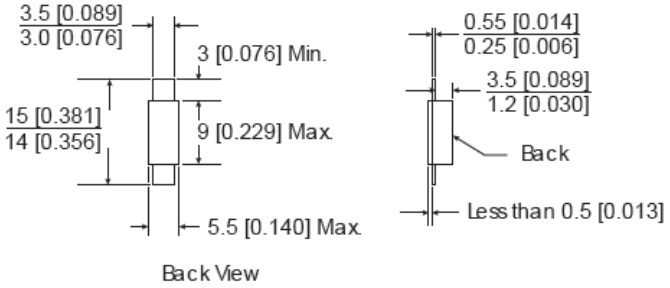
mils (mm)

B13



mils (mm)

B14



mils (mm)